

GM2308**N-CHANNEL ENHANCEMENT MODE POWER MOSFET**

BVDSS	60V
RDS(ON)	160mΩ
ID	3A

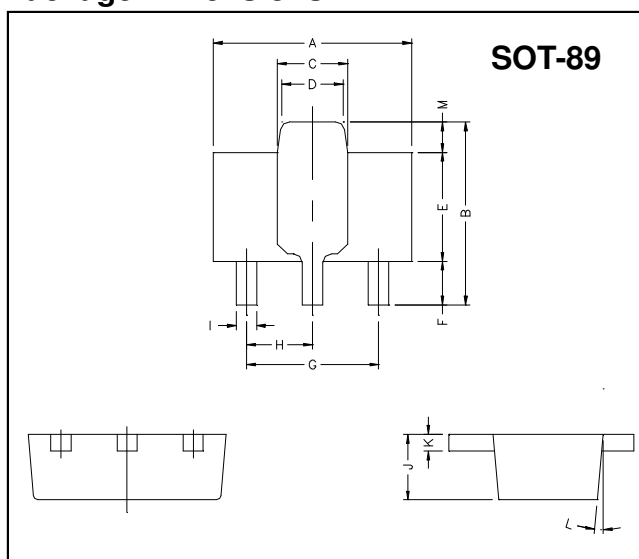
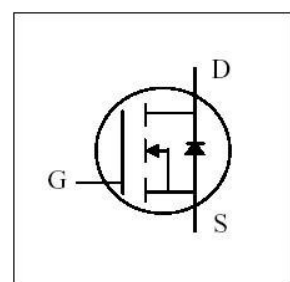
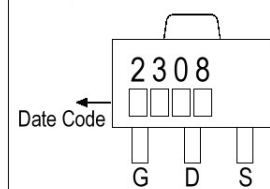
Description

The GM2308 utilized advanced processing techniques to achieve the lowest possible on-resistance, extremely efficient and cost-effectiveness device.

The GM2308 is universally used for all commercial-industrial surface mount applications.

Features

- *Simple Drive Requirement
- *Small Package Outline

Package Dimensions**Marking :**

REF.	Millimeter		REF.	Millimeter	
	Min.	Max.		Min.	Max.
A	4.4	4.6	G	3.00	REF.
B	4.05	4.25	H	1.50	REF.
C	1.50	1.70	I	0.40	0.52
D	1.30	1.50	J	1.40	1.60
E	2.40	2.60	K	0.35	0.41
F	0.89	1.20	L	5° TYP.	
			M	0.70 REF.	

Absolute Maximum Ratings

Parameter	Symbol	Ratings	Unit
Drain-Source Voltage	V_{DS}	60	V
Gate-Source Voltage	V_{GS}	± 20	V
Continuous Drain Current ³ , $V_{GS}@4.5V$	$I_D @TA=25^{\circ}C$	3.0	A
Continuous Drain Current ³ , $V_{GS}@4.5V$	$I_D @TA=70^{\circ}C$	2.3	A
Pulsed Drain Current ^{1,2}	I_{DM}	10	A
Power Dissipation	$P_D @TA=25^{\circ}C$	1.5	W
Linear Derating Factor		0.01	W/ $^{\circ}C$
Operating Junction and Storage Temperature Range	T_j, T_{stg}	-55 ~ +150	$^{\circ}C$

Thermal Data

Parameter	Symbol	Value	Unit
Thermal Resistance Junction-ambient ³ Max.	R_{thj-a}	83.3	$^{\circ}C/W$

Electrical Characteristics (T_j = 25°C unless otherwise specified)

Parameter	Symbol	Min.	Typ.	Max.	Unit	Test Conditions
Drain-Source Breakdown Voltage	BV _{DSS}	60	-	-	V	V _{GS} =0, I _D =250uA
Breakdown Voltage Temperature Coefficient	ΔBV _{DSS} / ΔT _j	-	0.05	-	V/°C	Reference to 25°C, I _D =1mA
Gate Threshold Voltage	V _{GS(th)}	1.0	-	3.0	V	V _{DS} =V _{GS} , I _D =250uA
Forward Transconductance	g _{fs}	-	5.0	-	S	V _{DS} =5V, I _D =3A
Gate-Source Leakage Current	I _{GSS}	-	-	±100	nA	V _{GS} = ±20V
Drain-Source Leakage Current(T _j =25°C)	I _{DSS}	-	-	10	uA	V _{DS} =60V, V _{GS} =0
Drain-Source Leakage Current(T _j =70°C)		-	-	25	uA	V _{DS} =48V, V _{GS} =0
Static Drain-Source On-Resistance	R _{DS(ON)}	-	-	160	mΩ	V _{GS} =10V, I _D =2.0A
		-	-	220		V _{GS} =4.5V, I _D =1.7A
Total Gate Charge ²	Q _g	-	6	10	nC	I _D =3A V _{DS} =48V V _{GS} =4.5V
Gate-Source Charge	Q _{gs}	-	1.6	-		
Gate-Drain ("Miller") Charge	Q _{gd}	-	3	-		
Turn-on Delay Time ²	T _{d(on)}	-	6	-	ns	V _{DS} =30V I _D =1A V _{GS} =10V R _G =3.3Ω R _D =30Ω
Rise Time	T _r	-	5	-		
Turn-off Delay Time	T _{d(off)}	-	16	-		
Fall Time	T _f	-	3	-		
Input Capacitance	C _{iss}	-	490	780	pF	V _{GS} =0V V _{DS} =25V f=1.0MHz
Output Capacitance	C _{oss}	-	55	-		
Reverse Transfer Capacitance	C _{rss}	-	40	-		

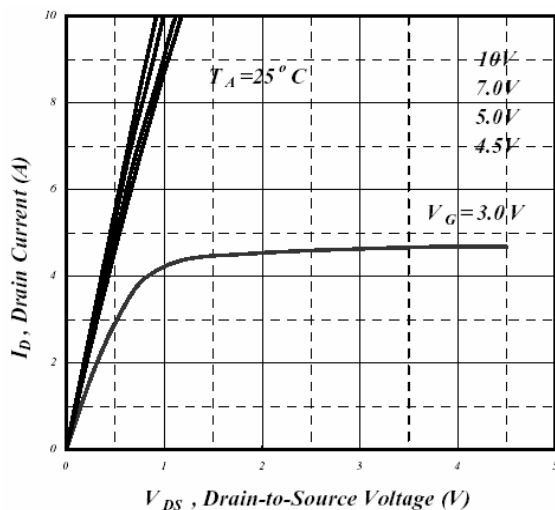
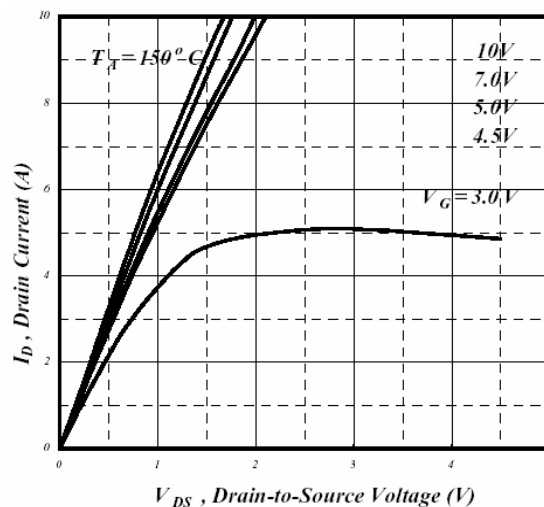
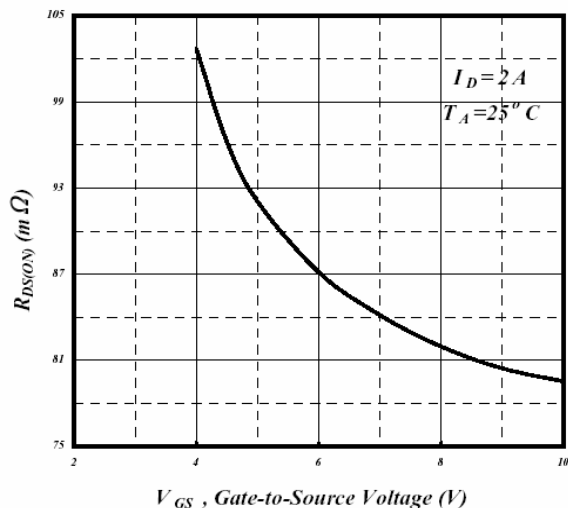
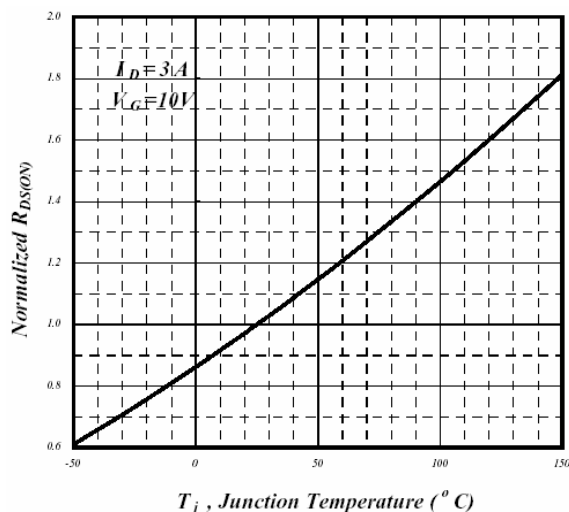
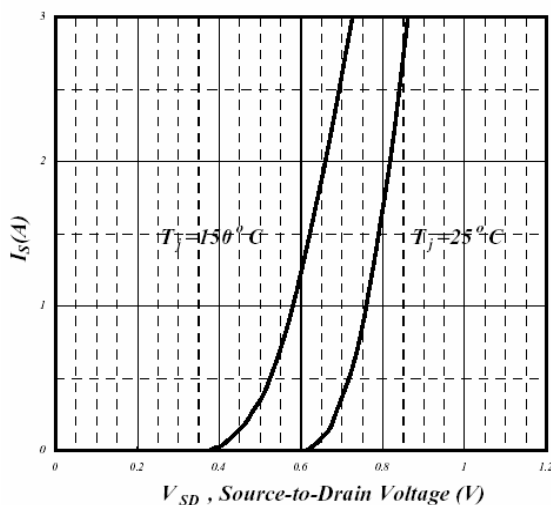
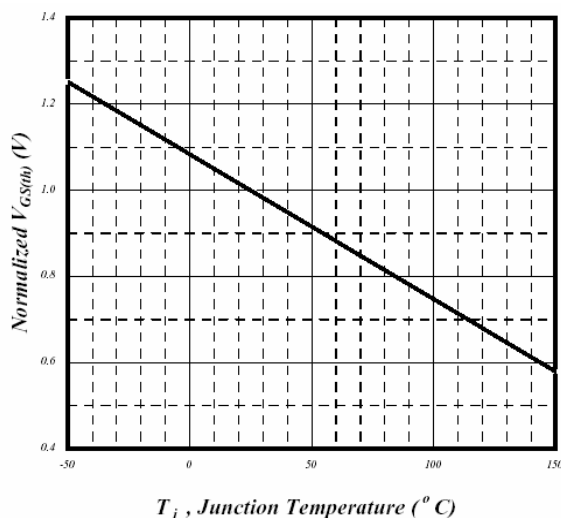
Source-Drain Diode

Parameter	Symbol	Min.	Typ.	Max.	Unit	Test Conditions
Forward On Voltage ²	V _{SD}	-	-	1.2	V	I _S =1.2A, V _{GS} =0V
Reverse Recovery Time	T _{rr}	-	25	-	ns	I _S =3A, V _{GS} =0V di/dt=100A/μs
Reverse Recovery Charge	Q _{rr}	-	26	-	nC	

Notes: 1. Pulse width limited by Max. junction temperature.

2. Pulse width ≤ 300us, duty cycle ≤ 2%.

3. Surface mounted on FR4 board, t ≤ 10sec.

Characteristics Curve**Fig 1. Typical Output Characteristics****Fig 2. Typical Output Characteristics****Fig 3. On-Resistance v.s. Gate Voltage****Fig 4. Normalized On-Resistance v.s. Junction Temperature****Fig 5. Forward Characteristics of Reverse Diode****Fig 6. Gate Threshold Voltage v.s. Junction Temperature**

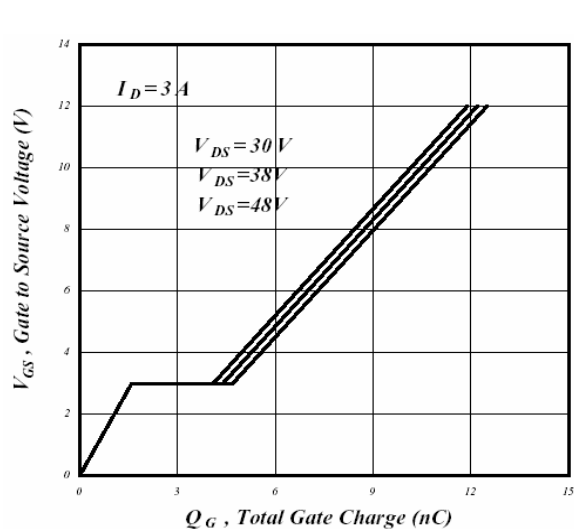


Fig 7. Gate Charge Characteristics

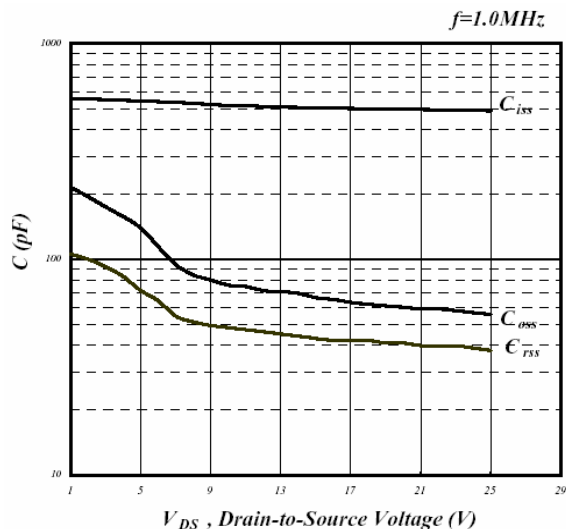


Fig 8. Typical Capacitance Characteristics

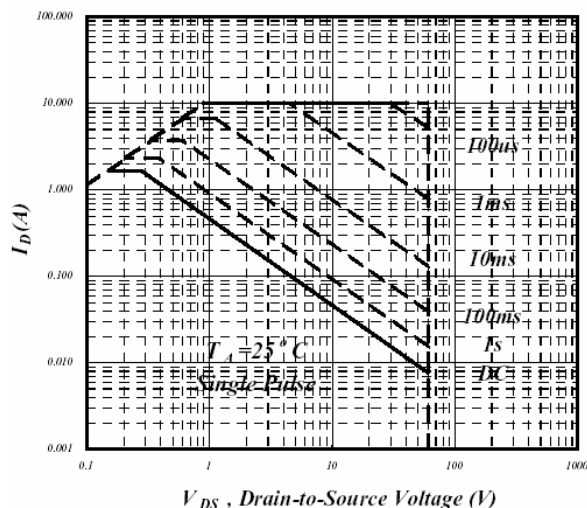


Fig 9. Maximum Safe Operating Area

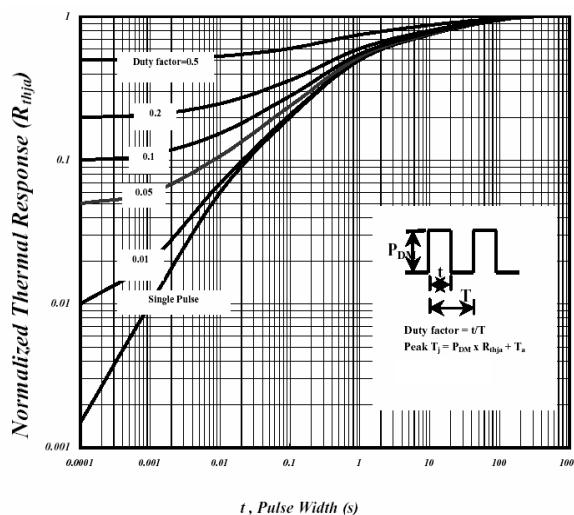


Fig 10. Effective Transient Thermal Impedance

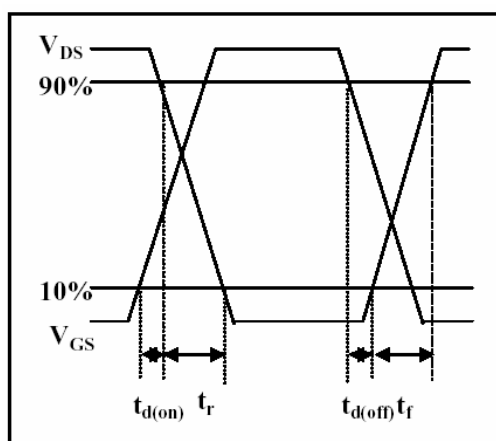


Fig 11. Switching Time Waveform

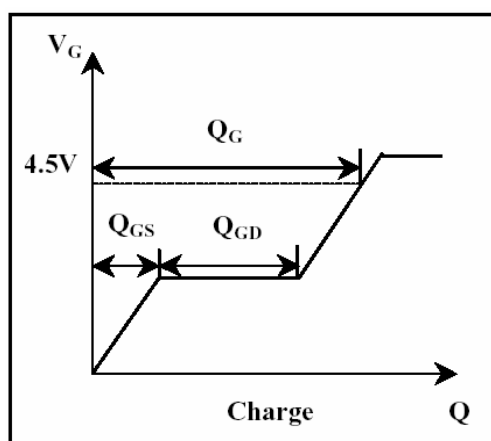


Fig 12. Gate Charge Waveform

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